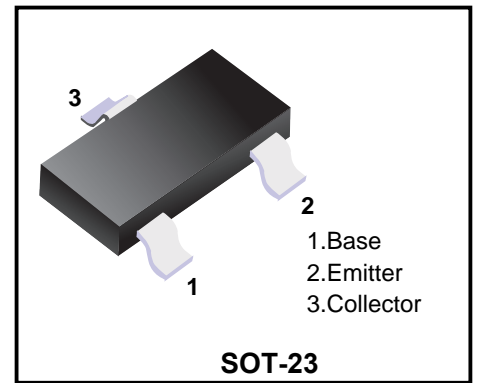


NPN Silicon Epitaxial Planar Darlington Transistor

FEATURES

- Epitaxial planar die construction.
- High current gain.



APPLICATIONS

- Ideal for medium power amplification and switching.

Marking Code	
MMBTA13	K2D

Absolute Maximum Ratings (Ta = 25 °C)

Parameter	Symbol	Value	Unit
Collector Emitter Voltage	V_{CES}	30	V
Collector Base Voltage	V_{CBO}	30	V
Emitter Base Voltage	V_{EBO}	10	V
Collector Current	I_C	500	mA
Total Device Dissipation Derate above 25 °C	P_{tot}	200	mW
		2.8	mW/°C
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	357	°C/W
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_s	-55 to +150	°C

Characteristics at $T_{amb}=25\text{ }^{\circ}\text{C}$

Parameter	Symbol	Min.	Max.	Unit
DC Current Gain at $I_C=10\text{mA}$, $V_{CE}=5\text{V}$ at $I_C=100\text{mA}$, $V_{CE}=5\text{V}$	h_{FE} h_{FE}	5000 10,000	- -	- -
Collector Cutoff Current at $V_{CB}=30\text{V}$	I_{CBO}	-	0.1	μA
Emitter Cutoff Current at $V_{EB}=10\text{V}$	I_{EBO}	-	0.1	μA
Collector Emitter Breakdown Voltage at $I_C=100\mu\text{A}$	$V_{(BR)CES}$	30	-	V
Collector Saturation Voltage at $I_C=100\text{mA}$, $I_B=0.1\text{mA}$	$V_{CE(sat)}$	-	1.5	V
Base On Voltage at $I_C=100\text{mA}$, $V_{CE}=5\text{V}$	$V_{BE(on)}$	-	2	V
Current Gain – Bandwidth Product at $I_C=10\text{mA}$, $V_{CE}=10\text{V}$, $f=100\text{MHz}$	f_T	125	-	MHz

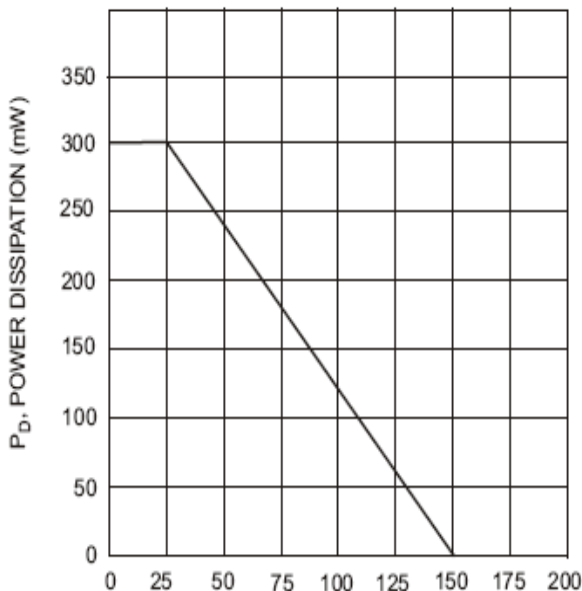
Ratings and Characteristic Curves


Fig. 1, Max Power Dissipation vs Ambient Temperature

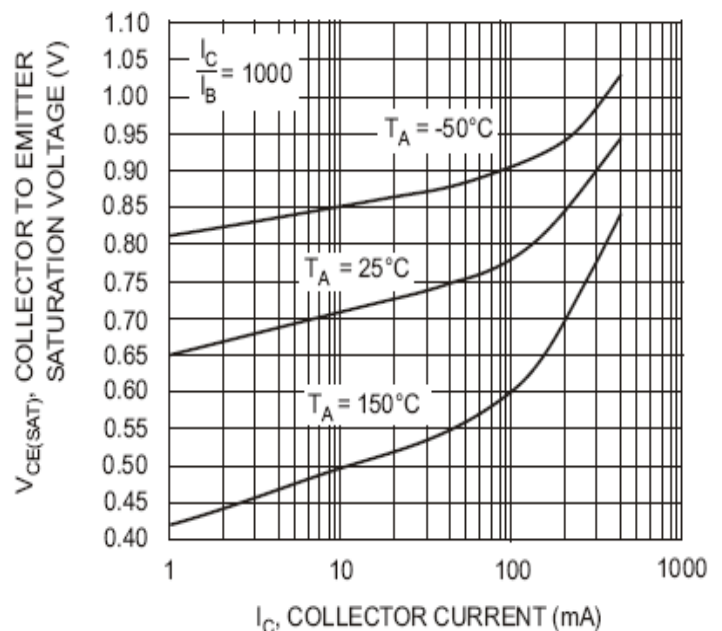


Fig. 2, Collector Emitter Saturation Voltage vs. Collector Current

Ordering information

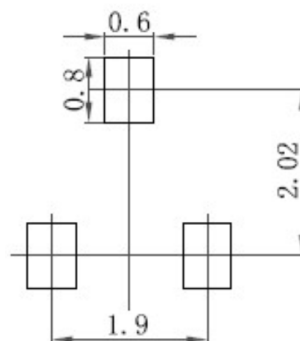
Package	Packing Description	Base Quantity	Packing Quantity
SOT-23	Tape/Reel,7"reel	3000pcs/Reel	24000PCS/Box 120000PCS/Carton

Package Dimensions

SOT-23

Dim.	Millimeter (mm)		mil	
	Min.	Max.	Min.	Max.
A	0.9	1.15	35	45
A1	0.1		3.9	
bp	0.38	0.48	15	19
C	0.09	0.15	3.54	5.9
D	2.8	3.0	110	118
E	1.2	1.4	47	55
E	1.9		75	
E1	0.95		37	
HE	2.1	2.55	83	100
Lp	0.15	0.45	5.9	18
Q	0.45	0.55	18	22
v	0.2		7.9	
W	0.1		4	

The recommended mounting pad size



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